BCD-To-Seven Segment Latch/Decoder/Driver

CMOS MSI (Low-Power Complementary MOS)

The MC14513B BCD–to–seven segment latch/decoder/driver is constructed with complementary MOS (CMOS) enhancement mode devices and NPN bipolar output drivers in a single monolithic structure. The circuit provides the functions of a 4–bit storage latch, an 8421 BCD–to–seven segment decoder, and has output drive capability. Lamp test (\overline{LT}), blanking (\overline{BI}), and latch enable (LE) inputs are used to test the display, to turn–off or pulse modulate the brightness of the display, and to store a BCD code, respectively. The Ripple Blanking Input (RBI) and Ripple Blanking Output (RBO) can be used to suppress either leading or trailing zeroes. It can be used with seven–segment light emitting diodes (LED), incandescent, fluorescent, gas discharge, or liquid crystal readouts either directly or indirectly.

Applications include instrument (e.g., counter, DVM, etc.) display driver, computer/calculator display driver, cockpit display driver, and various clock, watch, and timer uses.

- Low Logic Circuit Power Dissipation
- High-current Sourcing Outputs (Up to 25 mA)
- Latch Storage of Binary Input
- Blanking Input
- Lamp Test Provision
- Readout Blanking on all Illegal Input Combinations
- Lamp Intensity Modulation Capability
- Time Share (Multiplexing) Capability
- Adds Ripple Blanking In, Ripple Blanking Out to MC14511B
- Supply Voltage Range = 3.0 V to 18 V
- Capable of Driving Two Low-Power TTL Loads, One Low-power Schottky TTL Load to Two HTL Loads Over the Rated Temperature Range.

MAXIMUM RATINGS (Voltages Referenced to V_{SS}) (1.)

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage Range	-0.5 to +18.0	V
V _{in}	Input Voltage Range, All Inputs	-0.5 to $V_{DD} + 0.5$	V
I	DC Current Drain per Input Pin	10	mA
P _D	Power Dissipation, per Package ^(2.)	500	mW
T _A	Operating Temperature Range	-55 to +125	°C
T _{stg}	Storage Temperature Range	-65 to +150	°C
I _{OHmax}	Maximum Continuous Output Drive Current (Source) per Output	25	mA
P _{OHmax}	Maximum Continuous Output Power (Source) per Output (3.)	50	mW



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MARKING DIAGRAMS

PDIP-18 P SUFFIX CASE 707 MC14513BCP
O AWLYYWW

A = Assembly Location

WL or L = Wafer Lot YY or Y = Year WW or W = Work Week

ORDERING INFORMATION

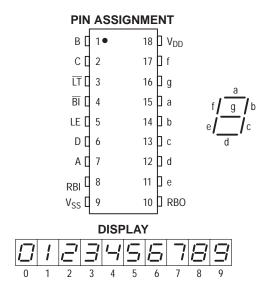
Device	Package	Shipping
MC14513BCP	PDIP-18	20/Rail

This device contains protection circuitry to protect the inputs against damage due to high static voltages or electric fields. However, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high-impedance circuit. A destructive high current mode may occur if V_{in} and V_{out} are not constrained to the range $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}.$

Due to the sourcing capability of this circuit, damage can occur to the device if V_{DD} is applied, and the outputs are shorted to V_{SS} and are at a logical 1 (See Maximum Ratings).

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}).

- Maximum Ratings are those values beyond which damage to the device may occur.
- Temperature Derating:
 Plastic "P and D/DW" Packages: 7.0 mW/°C
 From 65°C To 125°C
- 3. $P_{OHmax} = I_{OH} (V_{DD} V_{OH})$



TRUTH TABLE

Inputs								Outputs								
RBI	LE	BI	LT	D	С	В	Α	RBO	а	b	С	d	е	f	g	Display
Χ	Х	Χ	0	Χ	Χ	Χ	Χ	+	1	1	1	1	1	1	1	8
Х	Х	0	1	Χ	Χ	Χ	Χ	+	0	0	0	0	0	0	0	Blank
1	0	1	1	0	0	0	0	1	0	0	0	0	0	0	0	Blank
0	0	1	1	0	0	0	0	0	1	1	1	1	1	1	0	0
X	0	1	1	0	0	0	1	0	0	1	1	0	0	0	0	1
X	0	1	1	0	0	1	0	0	1	1	0	1	1	0	1	2
X	0	1	1	0	0	1	1	0	1	1	1	1	0	0	1	3
X	0	1	1	0	1	0	0	0	0	1	1	0	0	1	1	4
X	0	1	1	0	1	0	1	0	1	0	1	1	0	1	1	5
Х	0	1	1	0	1	1	0	0	1	0	1	1	1	1	1	6
X	0	1	1	0	1	1	1	0	1	1	1	0	0	0	0	7
X	0	1	1	1	0	0	0	0	1	1	1	1	1	1	1	8
X	0	1	1	1	0	0	1	0	1	1	1	1	0	1	1	9
X	0	1	1	1	0	1	0	0	0	0	0	0	0	0	0	Blank
X	0	1	1	1	0	1	1	0	0	0	0	0	0	0	0	Blank
X	0	1	1	1	1	0	0	0	0	0	0	0	0	0	0	Blank
X	0	1	1	1	1	0	1	0	0	0	0	0	0	0	0	Blank
X	0	1	1	1	1	1	0	0	0	0	0	0	0	0	0	Blank
Χ	0	1	1	1	1	1	1	0	0	0	0	0	0	0	0	Blank
Х	1	1	1	Х	Χ	Χ	Χ	†				*				*

X = Don't Care

†RBO = RBI ($\overline{D} \ \overline{C} \ \overline{B} \ \overline{A}$), indicated by other rows of table

*Depends upon the BCD code previously applied when LE = 0

ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

		V _{DD}	- 5	5°C		25°C			5°C	
Characteristic	Symbol	Vdc	Min	Max	Min	Тур (4.)	Max	Min	Max	Unit
Output Voltage — Segment Outputs "0" Level $V_{in} = V_{DD}$ or 0	V _{OL}	5.0 10 15	_ _ _	0.05 0.05 0.05	_ _ _	0 0 0	0.05 0.05 0.05	_ _ _	0.05 0.05 0.05	Vdc
$V_{in} = 0$ or V_{DD}	V _{OH}	5.0 10 15	4.1 9.1 14.1	_ _ _	4.1 9.1 14.1	5.0 10 15	_ _ _	4.1 9.1 14.1	_ _ _	Vdc
Output Voltage — RBO Output "0" Level V _{in} = V _{DD} or 0	V _{OL}	5.0 10 15	_ _ _	0.05 0.05 0.05	_ _ _	0 0 0	0.05 0.05 0.05	_ _ _	0.05 0.05 0.05	Vdc
$V_{in} = 0$ or V_{DD}	V _{OH}	5.0 10 15	4.95 9.95 14.95	_ _ _	4.95 9.95 14.95	5.0 10 15	_ _ _	4.95 9.95 14.95	_ _ _	Vdc
Input Voltage $^{(4.)}$ "0" Level $^{(V_O = 3.8 \text{ or } 0.5 \text{ Vdc})}$ $^{(V_O = 8.8 \text{ or } 1.0 \text{ Vdc})}$ $^{(V_O = 13.8 \text{ or } 1.5 \text{ Vdc})}$	V _{IL}	5.0 10 15	_ _ _	1.5 3.0 4.0	_ _ _	2.25 4.50 6.75	1.5 3.0 4.0	_ _ _	1.5 3.0 4.0	Vdc
$(V_O = 0.5 \text{ or } 3.8 \text{ Vdc})$ "1" Level $(V_O = 1.0 \text{ or } 8.8 \text{ Vdc})$ $(V_O = 1.5 \text{ or } 13.8 \text{ Vdc})$	V _{IH}	5.0 10 15	3.5 7.0 11	_ _ _	3.5 7.0 11	2.75 5.50 8.25	_ _ _	3.5 7.0 11	_ _ _	Vdc
Output Drive Voltage — Segments (I _{OH} = 0 mA) Source (I _{OH} = 5.0 mA) (I _{OH} = 10 mA) (I _{OH} = 15 mA) (I _{OH} = 20 mA) (I _{OH} = 25 mA)	V _{OH}	5.0	4.1 — 3.9 — 3.4 —	_ _ _ _ _	4.1 — 3.9 — 3.4 —	4.57 4.24 4.12 3.94 3.70 3.54	_ _ _ _ _	4.1 — 3.5 — 3.0 —		Vdc
(I _{OH} = 0 mA) (I _{OH} = 5.0 mA) (I _{OH} = 10 mA) (I _{OH} = 15 mA) (I _{OH} = 20 mA) (I _{OH} = 25 mA)		10	9.1 — 9.0 — 8.6 —	_ _ _ _ _	9.1 — 9.0 — 8.6 —	9.58 9.26 9.17 9.04 8.90 8.75	_ _ _ _ _	9.1 — 8.6 — 8.2 —	_ _ _ _ _	Vdc
(I _{OH} = 0 mA) (I _{OH} = 5.0 mA) (I _{OH} = 10 mA) (I _{OH} = 15 mA) (I _{OH} = 20 mA) (I _{OH} = 25 mA)		15	14.1 — 14 — 13.6 —	_ _ _ _ _	14.1 — 14 — 13.6 —	14.59 14.27 14.18 14.07 13.95 13.80	_ _ _ _ _	14.1 — 13.6 — 13.2 —	_ _ _ _ _	Vdc

(continued)

ELECTRICAL CHARACTERISTICS — continued (Voltages Referenced to V_{SS})

		V _{DD}	- 5	5°C	25°C			125	5°C	
Characteristic	Symbol	Vdc	Min	Max	Min	Typ ^(4.)	Max	Min	Max	Unit
Output Drive Current — RBO Output $(V_{OH} = 2.5 \text{ V})$ Source $(V_{OH} = 9.5 \text{ V})$ $(V_{OH} = 13.5 \text{ V})$	I _{OH}	5.0 10 15	- 0.40 - 0.21 - 0.81	_ _ _	- 0.32 - 0.17 - 0.66	- 0.64 - 0.34 - 1.30	_ _ _	- 0.22 - 0.12 - 0.46	_ _ _	mAdc
$(V_{OL} = 0.4 \text{ V})$ Sink $(V_{OL} = 0.5 \text{ V})$ $(V_{OL} = 1.5 \text{ V})$	I _{OL}	5.0 10 15	0.18 0.47 1.80	_ _ _	0.15 0.38 1.50	0.29 0.75 2.90	_ _ _	0.10 0.26 1.0	_ _ _	mAdc
Output Drive Current — Segments	I _{OL}	5.0 10 15	0.64 1.6 4.2	 	0.51 1.3 3.4	0.88 2.25 8.8	_ _ _	0.36 0.9 2.4	_ _ _	mAdc
Input Current	l _{in}	15	_	± 0.1		±0.00001	± 0.1	_	± 1.0	μAdc
Input Capacitance	C _{in}	_	_	_		5.0	7.5	_	_	pF
Quiescent Current (Per Package) $V_{in} = 0$ or V_{DD} , $I_{out} = 0 \mu A$	I _{DD}	5.0 10 15	_ _ _	5.0 10 20	_ _ _	0.005 0.010 0.015	5.0 10 20	_ _ _	150 300 600	μAdc
Total Supply Current (5.) (6.) (Dynamic plus Quiescent, Per Package) (C _L = 50 pF on all outputs, all buffers switching)	I _T	5.0 10 15			$I_T = (3$	I.9 μΑ/kHz) f 3.8 μΑ/kHz) f 5.7 μΑ/kHz) f	+ I _{DD}			μAdc

^{4.} Noise immunity specified for worst-case input combination.

Noise Margin for both "1" and "0" level =

1.0 Vdc min @ V_{DD} = 5.0 Vdc 2.0 Vdc min @ V_{DD} = 10 Vdc 2.5 Vdc min @ V_{DD} = 15 Vdc

6. To calculate total supply current at loads other than 50 pF:

$$I_T(C_L) = I_T(50 \text{ pF}) + 3.5 \text{ x } 10^{-3} (C_L - 50) \text{ V}_{DD}f$$

where: I_T is in μA (per package), C_L in pF, V_{DD} in Vdc, and f in kHz is input frequency.

Input LE and RBI low, and Inputs D, BI and LT high. f in respect to a system clock. All outputs connected to respective C_L loads.

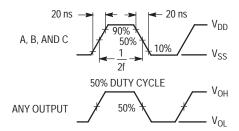


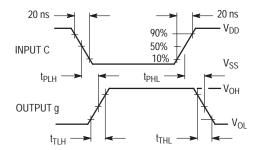
Figure 1. Dynamic Power Dissipation Signal Waveforms

^{5.} The formulas given are for the typical characteristics only at 25 $^{\circ}\text{C}.$

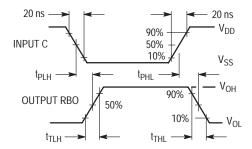
SWITCHING CHARACTERISTICS (7.) $(C_L = 50 \text{ pF}, T_A = 25^{\circ}C)$

		V _{DD}		All Types		
Characteristic	Symbol	Vdc	Min	Тур	Max	Unit
Output Rise Time — Segment Outputs	t _{TLH}	5.0 10 15	_ _ _	40 30 25	80 60 50	ns
Output Rise Time — RBO Output	t _{TLH}	5.0 10 15	_ _ _	480 240 190	960 480 380	ns
Output Fall Time — Segment Outputs $^{(7.)}$ $t_{THL} = (1.5 \text{ ns/pF}) C_L + 50 \text{ ns}$ $t_{THL} = (0.75 \text{ ns/pF}) C_L + 37.5 \text{ ns}$ $t_{THL} = (0.55 \text{ ns/pF}) C_L + 37.5 \text{ ns}$	t _{THL}	5.0 10 15	_ _ _	125 75 65	250 150 130	ns
Output Fall Time — RBO Outputs $t_{THL} = (3.25 \text{ ns/pF}) C_L + 107.5 \text{ ns}$ $t_{THL} = (1.35 \text{ ns/pF}) C_L + 67.5 \text{ ns}$ $t_{THL} = (0.95 \text{ ns/pF}) C_L + 62.5 \text{ ns}$	t _{THL}	5.0 10 15	_ _ _	270 135 110	540 270 220	ns
Propagation Delay Time — A, B, C, D Inputs $^{(7.)}$ $t_{PLH} = (0.40 \text{ ns/pF}) C_L + 620 \text{ ns}$ $t_{PLH} = (0.25 \text{ ns/pF}) C_L + 237.5 \text{ ns}$ $t_{PLH} = (0.20 \text{ ns/pF}) C_L + 165 \text{ ns}$	^t PLH	5.0 10 15	_ _ _	640 250 175	1280 500 350	ns
t_{PHL} = (1.3 ns/pF) C_L + 655 ns t_{PHL} = (0.60 ns/pF) C_L + 260 ns t_{PHL} = (0.35 ns/pF) C_L + 182.5 ns	t _{PHL}	5.0 10 15	_ _ _	720 290 200	1440 580 400	ns
Propagation Delay Time — RBI and \overline{BI} Inputs ^(7.) $t_{PLH} = (1.05 \text{ ns/pF}) C_L + 547.5 \text{ ns}$ $t_{PLH} = (0.45 \text{ ns/pF}) C_L + 177.5 \text{ ns}$ $t_{PLH} = (0.30 \text{ ns/pF}) C_L + 135 \text{ ns}$	t _{PLH}	5.0 10 15	_ _ _	600 200 150	750 300 220	ns
t_{PHL} = (0.85 ns/pF) C_L + 442.5 ns t_{PHL} = (0.45 ns/pF) C_L + 177.5 ns t_{PHL} = (0.35 ns/pF) C_L + 142.5 ns	[†] PHL	5.0 10 15	_ _ _	485 200 160	970 400 320	ns
Propagation Delay Time — $\overline{\text{LT}}$ Input ^(7.) $t_{\text{PLH}} = (0.45 \text{ ns/pF}) \text{ C}_{\text{L}} + 290.5 \text{ ns}$ $t_{\text{PLH}} = (0.25 \text{ ns/pF}) \text{ C}_{\text{L}} + 112.5 \text{ ns}$ $t_{\text{PLH}} = (0.20 \text{ ns/pF}) \text{ C}_{\text{L}} + 80 \text{ ns}$	^t PLH	5.0 10 15	_ _ _	313 125 90	625 250 180	ns
t_{PHL} = (1.3 ns/pF) C_L + 248 ns t_{PHL} = (0.45 ns/pF) C_L + 102.5 ns t_{PHL} = (0.35 ns/pF) C_L + 72.5 ns	[†] PHL	5.0 10 15	_ _ _	313 125 90	625 250 180	ns
Setup Time	t _{su}	5.0 10 15	100 40 30	_ _ _	_ _ _	ns
Hold Time	t _h	5.0 10 15	60 40 30	_ _ _	_ _ _	ns
Latch Enable Pulse Width	t _{WL(LE)}	5.0 10 15	520 220 130	260 110 65	_ _ _	ns

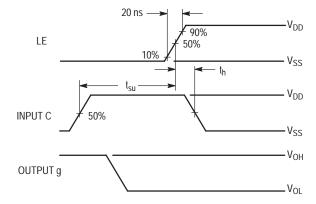
^{7.} The formulas given are for the typical characteristics only.



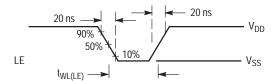
a. Data Propagation Delay: Inputs RBI, D and LE low, and Inputs A, B, $\overline{\text{BI}}$ and $\overline{\text{LT}}$ high.



b. Inputs A, B, D and LE low, and Inputs RBI, $\overline{\text{BI}}$ and $\overline{\text{LT}}$ high.



c. Setup and Hold Times: Input RBI and D low, Inputs A, B, $\overline{\text{BI}}$ and $\overline{\text{LT}}$ high.

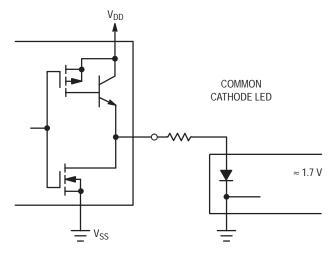


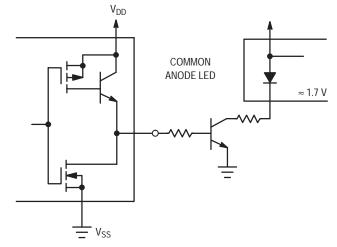
d. Pulse Width: Data DCBA strobed into latches.

Figure 2. Dynamic Signal Waveforms

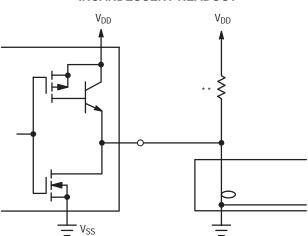
CONNECTIONS TO VARIOUS DISPLAY READOUTS

LIGHT EMITTING DIODE (LED) READOUT

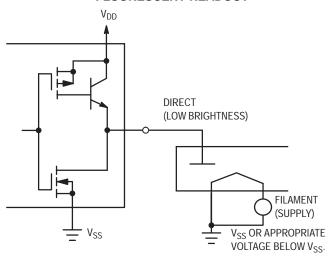




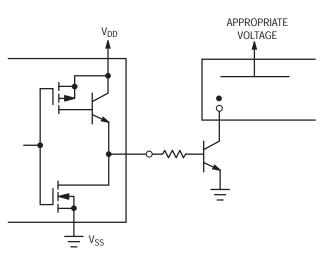
INCANDESCENT READOUT



FLUORESCENT READOUT

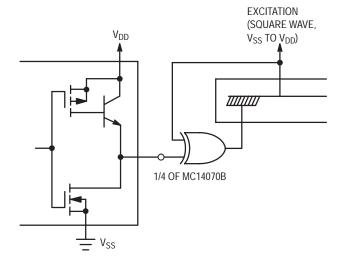


GAS DISCHARGE READOUT



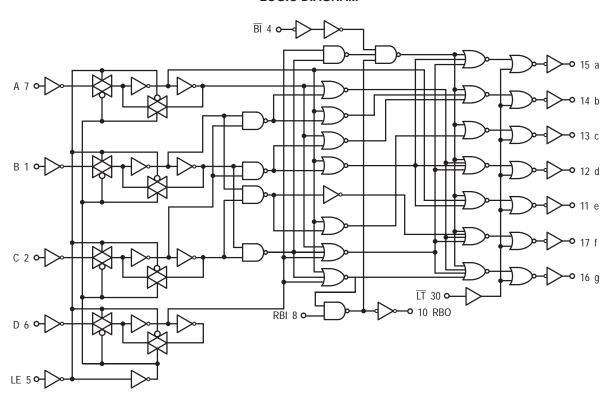
** A filament pre—warm resistor is recommended to reduce filament thermal shock and increase the effective cold resistance of the filament.

LIQUID CRYSTAL (LC) READOUT



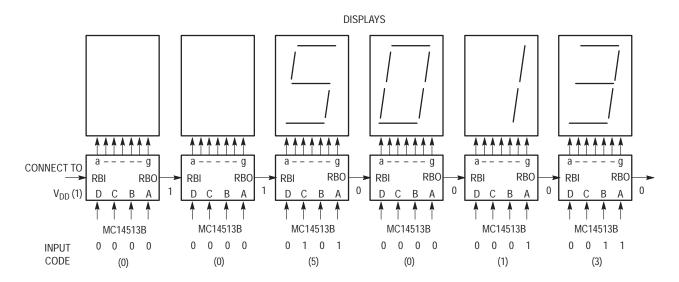
Direct dc drive of LC's not recommended for life of LC readouts.

LOGIC DIAGRAM

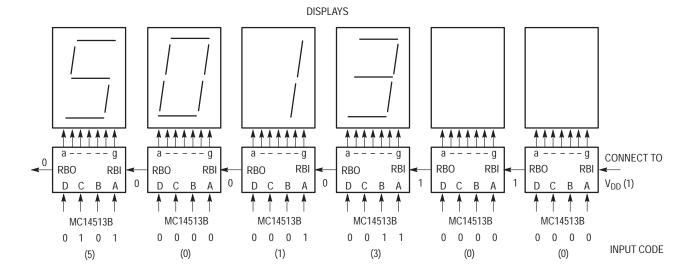


TYPICAL APPLICATIONS FOR RIPPLE BLANKING

LEADING EDGE ZERO SUPPRESSION

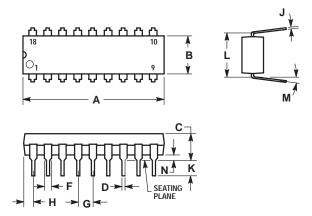


TRAILING EDGE ZERO SUPPRESSION



PACKAGE DIMENSIONS

PDIP-18 **P SUFFIX** PLASTIC DIP PACKAGE CASE 707-02 ISSUE C



- NOTES:

 1. POSITIONAL TOLERANCE OF LEADS (D), SHALL BE WITHIN 0.25 (0.010) AT MAXIMUM MATERIAL CONDITION, IN RELATION TO SEATING PLANE AND EACH OTHER.

 2. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.

 3. DIMENSION B DOES NOT INCLUDE MOLD FLASH.

 4. CONTROLLING DIMENSION: INCH.

	INC	HES	MILLIM	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.875	0.915	22.22	23.24	
В	0.240	0.260	6.10	6.60	
С	0.140	0.180	3.56	4.57	
D	0.014	0.022	0.36	0.56	
F	0.050	0.070	1.27	1.78	
G	0.100	BSC	2.54 BSC		
Н	0.040	0.060	1.02	1.52	
J	0.008	0.012	0.20	0.30	
K	0.115	0.135	2.92	3.43	
Г	0.300) BSC	7.62 BSC		
M	0 °	15°	0 °	15°	
N	0.020	0.040	0.51	1.02	

Notes

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